

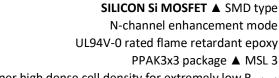




100V ▲ 98mΩ ▲ 10A ▲ Si MOSFET









Super high dense cell density for extremely low R_{DS(ON)} **High power and current handling capability**

MAXIMUM RATINGS

Parameter (T _c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	100V
Gate-Source Voltage	V _{GS}	±16V
Continuous Drain Current at R _{TH_JC}	I _D	10A
Continuous Drain Current at R _{TH_JA}	I _D	2A
Pulsed Drain Current at R _{TH_JC} Note 1	I _{DM}	40A
Pulsed Drain Current at R _{TH_JA} Note 1	I _{DM}	8A
Maximum Power Dissipation	P _D	25W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

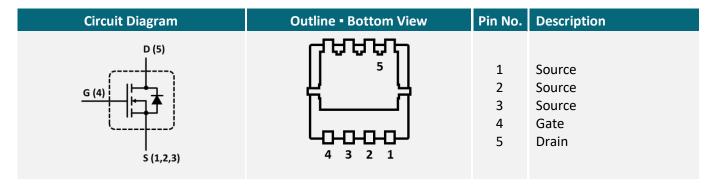
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	50°C/W

APPLICATIONS

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+4-	50			

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV_{DSS}	100			V
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	I _{DSS}			10	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	$V_{GS(th)}$	0.4		1.4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 6A$	R _{DS(ON)}		98	120	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 5V$, $I_D = 6A$	R _{DS(ON)}		103	130	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 3V$, $I_D = 3A$	R _{DS(ON)}		120	165	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		535		pF
Output Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		160		pF
Reverse Transfer Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	C_{RSS}		45		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 3A, $R_{G(ext)}$ = 6Ω	t _{D(ON)}		8		ns
Turn-On Rise Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 3A, $R_{G(ext)}$ = 6Ω	t _R		4		ns
Turn-Off Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 3A, $R_{G(ext)}$ = 6Ω	t _{D(OFF)}		35		ns
Turn-Off Fall Time	V_{DD} = 50V, V_{GS} = 10V, I_D = 3A, $R_{G(ext)}$ = 6Ω	t _F		4		ns
Total Gate Charge	V_{DS} = 80V, V_{GS} = 4.5V, I_{D} = 3A	Q_{G}		9.5		nC
Gate Source Charge	$V_{DS} = 80V$, $V_{GS} = 4.5V$, $I_{D} = 3A$	Q_{GS}		1		nC
Gate Drain Charge	$V_{DS} = 80V$, $V_{GS} = 4.5V$, $I_{D} = 3A$	Q_GD		4		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		Is			10	Α
Drain-Source Diode Forward Voltage Note 3	$V_{GS} = 0V$, $I_S = 10A$	V_{SD}			1.5	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

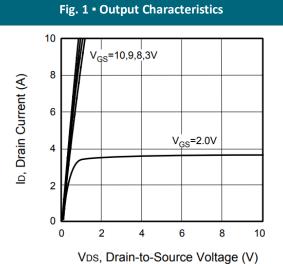


Fig. 2 • Transfer Characteristics

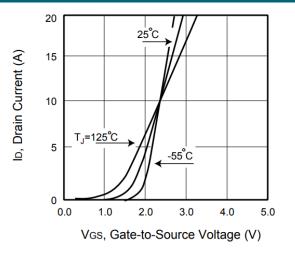


Fig. 3 • Capacitance

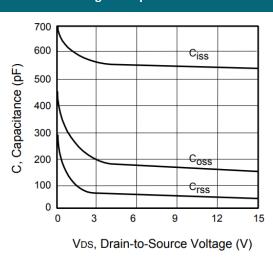


Fig. 4 • On-Resistance Variation with Temperature

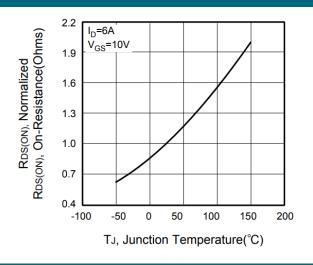


Fig. 5 • Gate Threshold Variation with Temperature

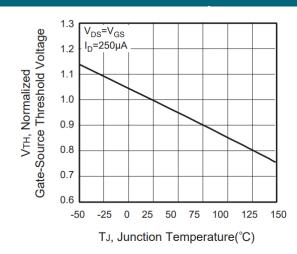
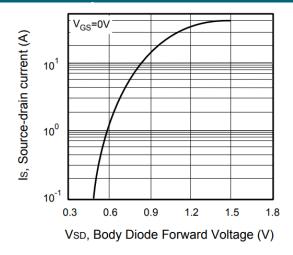


Fig. 6 • Body Diode Forward Voltage Variation with Source Current





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

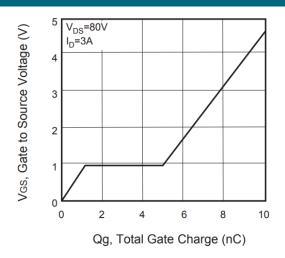


Fig. 8 • Maximum Safe Operating Area

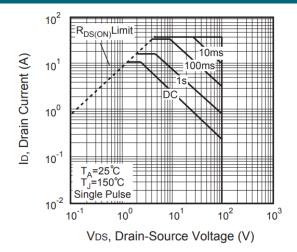


Fig. 9 • Breakdown Voltage Variation vs. Temperature

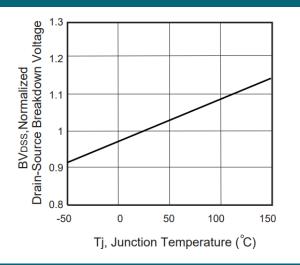


Fig. 10 • Switching Test Circuit

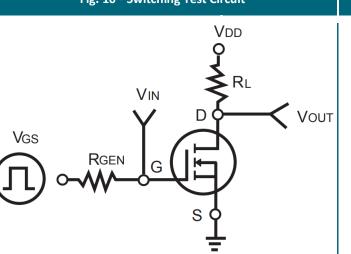
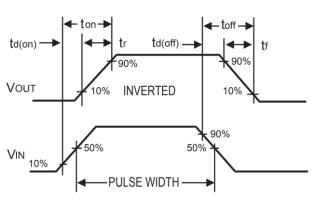


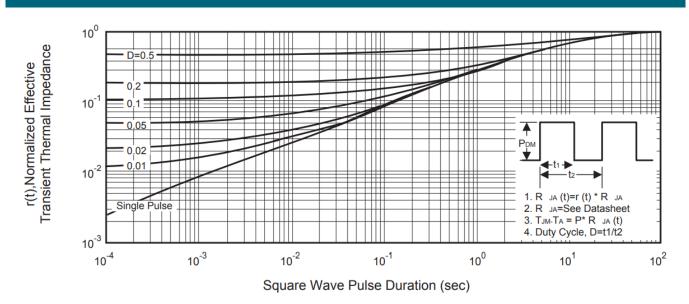
Fig. 11 • Switching Waveforms



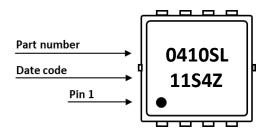


REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve



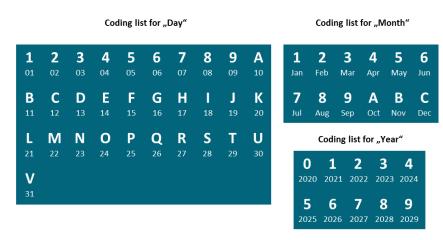
PART MARKING



DATE CODE

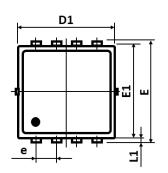
Example: 11S4Z

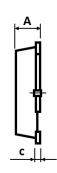


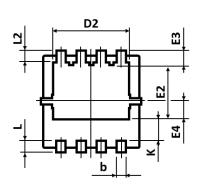


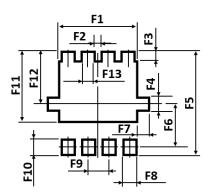


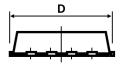
PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT











Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
Λ	0.700		0.850	
Α	0.700	-	0.850	
b	0.200	-	0.400	
С	0.100	-	0.250	
D	3.000	-	3.450	
D1	3.000	-	3.250	
D2	2.290	-	2.650	
E	3.150	-	3.450	
E1	2.900	-	3.200	

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
E2	1.540	-	1.940
E3	0.280	-	0.650
E4	0.370	-	0.770
е		0.650 (BSC)	
K	0.500	-	0.890
L	0.300	-	0.500
L1	0.060	-	0.200
L2	0.270	-	0.570

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
F4		2.500		
F1	-	2.500	-	
F2	-	0.300	-	
F3	-	0.400	-	
F4	-	0.430	-	
F5	-	3.350	-	
F6	-	1.400	-	
F7	_	0.420	_	

Sym	Millimeters Millimeters (Min.) (Typ.)		Millimeters (Max.)
F8	-	0.350	-
F9	-	0.650	-
F10	-	0.500	-
F11	-	2.280	-
F12	-	1.700	-
F13	-	0.350	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

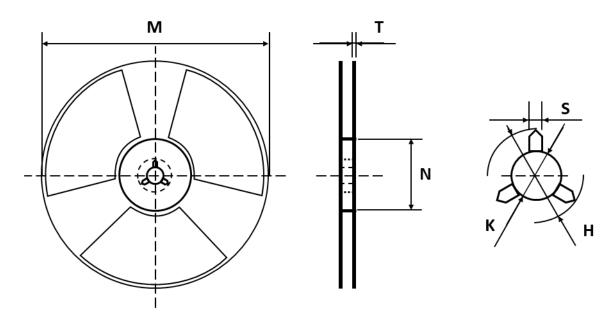
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEZC0410SL	PPAK 3x3	Reel	5,000pcs	10,000pcs	80,000pcs

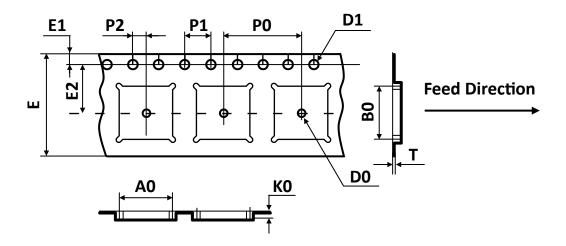


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
12mm	Ø330	±2.00	±1.00	±0.20	±0.50	+0.50 -0.20	±0.50

TAPE DIMENSIONS ▲ All dimensions in mm

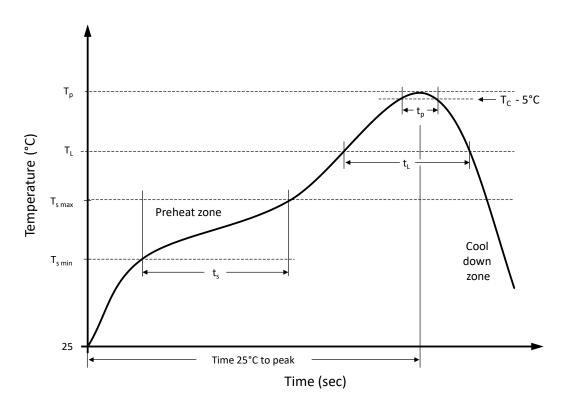


Package	Α0	В0	КО	D0	D1	E	E1	E2	P0	P1	P2	T
	6.50	5.28	2.00	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
PPAK 3x3	±0.10	±0.10	±0.10	±0.25	±0.10	+0.30	±0.10	±0.05	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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